HAMAMATSU

PHOTON IS OUR BUSINESS

PHOTOMULTIPLIER TUBE R13456

FEATURES

High sensitivity



Biomedical analysis

- Blood analyzer, Flow cytometer, DNA sequencer •Environmental monitoring
- NOx analyzer

Spectroscopy

Fluorescence spectrometer, Raman spectrometer, UV–VIS-NIR spectrometer

Microscopy

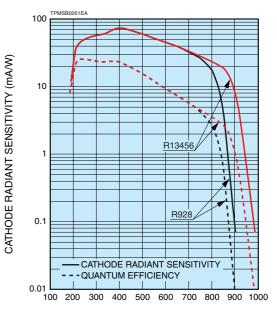
SPECIFICATIONS

GENERAL

Pa	rameter	Description / Value	Unit		
Spectral respon	nse	185 to 980	nm		
Wavelength of	maximum response	400	nm		
Photocathode	Material	Multialkali	—		
Filotocatiloue	Minimum effective area	8×24	mm		
Window materi	al	UV glass	_		
Dynode	Structure	Circular-cage	_		
Dynoue	Number of stages	9	_		
Direct interelectrode	Anode to last dynode	4	рF		
capacitances	Anode to all other electrodes	6	pF		
Base		11-pin base JEDEC No. B11-88	_		
Weight		Approx. 45	g		
Operating amb	ient temperature	-30 to +50	°C		
Storage tempe	rature	-30 to +50	°C		
Suitable socke	t	E678–11A (Sold separately)	_		
Suitable socke	tassembly	E717–63 (Sold separately)			
	assembly	E717–74 (Sold separately)			



Figure 1: Typical spectral response



WAVELENGTH (nm)

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MAXIMUM RATINGS (Absolute maximum values)

	Parameter	Value						
Supply voltage	Between anode and cathode	1250	V					
	Between anode and last dynode	250	V					
Average anode curre	ent ^A	0.1	mA					

CHARACTERISTICS (at 25 °C)

	Parameter		Min.	Тур.	Max.	Unit
	Quantum efficience	y at 900 nm	0.3	1	_	%
	Luminous ^B		140	280		μA/Im
		at 194 nm	_	18		mA/W
		at 254 nm	_	52		mA/W
Cathode sensitivity	Radiant	at 400 nm		74		mA/W
		at 633 nm		41		mA/W
		at 852 nm	_	18		mA/W
	Red/White ratio ^C		0.3	0.4	_	-
	Blue sensitivity ind	ex ^D	_	8	_	_
	Luminous ^E		400	2800		A/Im
		at 194 nm	_	$1.8 imes10^5$		A/W
Anodo oppoitivity	Radiant	at 254 nm	—	5.2 × 10 ⁵	_	A/W
Anode sensitivity		at 400 nm	_	$7.4 imes10^5$	_	A/W
		at 633 nm	_	4.1 × 10 ⁵	_	A/W
		at 852 nm	—	$1.8 imes10^5$	_	A/W
Gain ^E			—	$1.0 imes 10^{7}$	_	—
Anode dark current ^F (After 30 min storage in darkness)			_	5	50	nA
ENI (Equivalent Noise Input) G				$1.7 imes 10^{-16}$		W
	Anode pulse rise ti	me ^H	_	2.2	_	ns
Time response	Electron transit tim	ie ⁱ	_	22	_	ns
	Transit time spread	d (T.T.S.) ^J	_	1.2		ns

NOTES

A: Averaged over any interval of 30 s maximum.

- B: The light source is a tungsten filament lamp operated at a distribution temperature of 2856 K. Supply voltage is 100 V between the cathode and all other electrodes connected together as anode.
- C:Red/White ratio is the quotient of the cathode current measured using a red filter(Toshiba R-68) interposed between the light source and the tube by the cathode current measured with the filter removed under the same conditions as Note B.
- D: The value is cathode output current when a blue filter (Corning CS 5-58 polished to 1/2 stock thickness) is interposed between the light source and the tube under the same condition as Note B.
- E: Measured with the voltage distribution ratio shown in Table 1 below.

Table 1:Voltage distribution ratio

	Electrode	ł	<	Dy	y1 Dy		/2 Dy3		3	Dy4		Dy5		Dye	5 D	Dy7		y8	Dy9			Р
	Distribution ratio		1		-	1		1 1		1	1		-	1	1		1		1	1		
Supply voltage: 1000 V, K: Cathode, Dy: Dynode, P: Anod											de											

F: Measured with the same supply voltage and voltage distribution ratio as Note E after removal of light.

G: ENI is an indication of the photon-limited signal-to-noise ratio. It refers to the amount of light in watts to produce a signal-to-noise ratio of unity in the output of a photomultiplier tube.

$$\mathsf{ENI} = \frac{\sqrt{2q} \cdot \mathsf{Idb} \cdot \mathbf{G} \cdot \Delta \mathbf{f}}{\mathsf{S}}$$

where $q = Electronic charge (1.60 \times 10^{-19} coulomb).$

- ldb = Anode dark current(after 30 min storage) in amperes. G = Gain.
 - Δf = Bandwidth of the system in hertz. 1 Hz is used.
 - S = Anode radiant sensitivity in amperes per watt at the wavelength of peak response.
- H: The rise time is the time for the output pulse to rise from 10 % to 90 % of the peak amplitude when the entire photocathode is illuminated by a delta function light pulse.
- I: The electron transit time is the interval between the arrival of delta function light pulse at the entrance window of the tube and the time when the anode output reaches the peak amplitude. In measurement, the whole photo-cathode is illuminated.
- J: Also called transit time jitter. This is the fluctuation in electron transit time between individual pulses in the signal photoelectron mode, and may be defined as the FWHM of the frequency distribution of electron transit times.



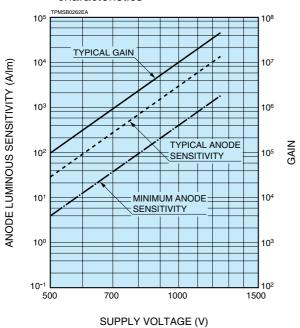


Figure 2: Anode luminous sensitivity and gain characteristics

Figure 4: Typical temperature coefficient of anode sensitivity

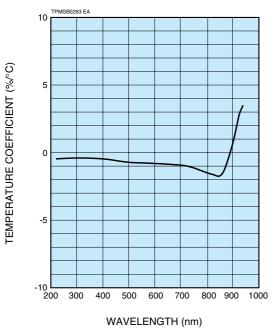


Figure 3: Typical time response

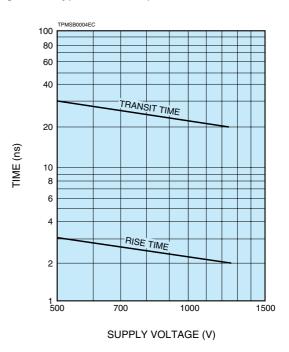
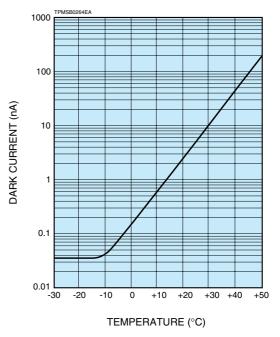


Figure 5: Typical temperature characteristic of dark current (at 1000 V, after 30 min storage in darkness)



8 MIN 49 38 PHOTOCATHODE DY6 DY5 DY7 6 3 DY8 24 MIN. 0 (9) DY9 80 MAX. DV3(3 **94 MAX** 2.5 DY2 D١ ¢29 49.0 ± DIRECTION OF LIGHT Bottom View 00 (Basing Diagram) φ32.2 ± 0.5 11 PIN BASE JEDEC No. B11-88 TACCA0064EA TPMSA0008EA Sold separately Figure 8: D type socket assembly (Unit: mm) E717-63 E717-74 HOUSING (INSULATOR) SOCKET SOCKET PIN No. ′ ° o PMT PMT • SIGNAL GND φ 0 3.5 33.0 ± 0.3 -(10) SIGNAL OUTPUT RG-174/U(BLACK) 32.0±0.5 -(10)-SIGNAL OUTPUT (A) <u>-0</u> 26.0±0.2 С \triangle _ ъŢ Р • GND (G) POWER SUPPLY GND AWG22 (BLACK) r₀ ° ٠i 0 R10 ± C3 0 ≹Β10 : C3 -9 DY9 H DY -9 R9 ≹R9 : C2 38.0 ± 0.3 26.0±0.2 -(8) (8) DY8 DY 49.0 ± 0.3 ≹R8 B8 C. 32.0±0.5 C. $\overline{(7)}$ DY TOP VIEW . ≹R7 ŚR7 φ29.0 ± 0.3 DY -6 -6 DY6 R1 to R10 : 330 kΩ ÅR6 R6 0+0 -(5) R1 to R10 : 330 kΩ C1 to C3 : 10 nF C1 to C3 : 10 nF DY5 DY5 -5 R5 ₹R5 0.7 A 30.0 ±0 -(4) DY4 -(4) G _____K φ31.0±0.5 ≹R4 -(3) HOUSING (INSULATOR) -(3) DY3 nν SIDE VIEW B3 . ≹R3 2 DY2 -@ Ц 450 ± 10 ŚR2 ÅR2 POTTING COMPOUND φ0.7 DY -(1) -① DY1 ≱R1 ≹R1 κ æ -11)--HV AWG22 (VIOLET) • -HV (K) \checkmark -11) 4- ø2.8 R13 "Wiring diagram applies when -HV is supplied." To supply +HV,connect the pin "G" to+HV, and the pin "K" to the GND. 4 BOTTOM VIEW TACCA0277EA * Hamamatsu also provides C4900 series compact high voltage power supplies and C12597-01 series DP type socket assemblies which incorporate a DC to DC converter type high voltage power supply. Warning-Personal safety hazards Electrical Shock-Operating voltages applied to this device present a shock hazard.

Figure 7: Socket (Unit: mm) Sold separately

E678-11A

Figure 6: Dimensional outline and basing diagram (Unit: mm)

 $\phi 28.5 \pm 1.5$

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